



40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C	
40V	7.5mΩ @ V _{GS} = 10V	62A	

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

- Power management functions
- DC-DC converters
- Backlighting

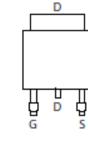
Features

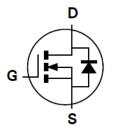
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low RDS(ON) Minimizes Power Losses
- Low Q_q –Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: TO252
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.33 grams (Approximate)







Top View

Pin Out Top View

Equivalent Circuit

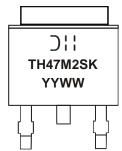
Ordering Information (Note 4)

Part Number	Package	Packing		
Part Number	Fackage	Qty.	Carrier	
DMTH47M2SK3-13	TO252 (DPAK)	2.500	Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



DII = Manufacturer's Marking
TH47M2SK = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 22 = 2022)
WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	VDSS	40	V
Gate-Source Voltage	Vgss	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 6)	I _D	62 44	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ірм	240	Α
Maximum Continuous Body Diode Forward Current (Note 6)	Is	60	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	240	Α
Avalanche Current, L = 0.1mH	I _{AS}	24.7	А
Avalanche Energy, L = 0.1mH	Eas	30.5	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	3.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	43	°C/W
Total Power Dissipation (Note 6)	Tc = +25°C	PD	50	W
Thermal Resistance, Junction to Case (Note 6)	R _θ JC	3	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C	

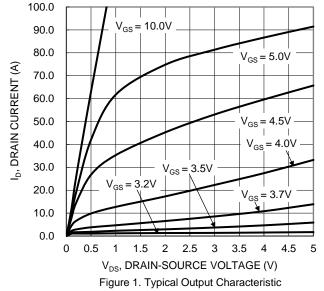
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

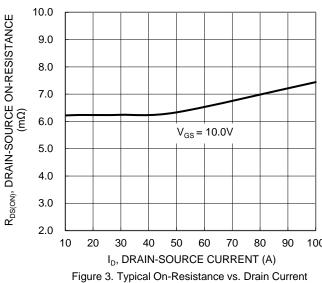
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V _{DS} = 32V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	6.2	7.5	mΩ	$V_{GS} = 10V, I_D = 20A$	
Diode Forward Voltage	VsD	_	0.9	1.2	V	Vgs = 0V, Is = 20A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	897	_		V _{DS} = 20V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	530	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	12.4	_			
Gate Resistance	Rg	_	2.07	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	12.1	_			
Gate-Source Charge	Qgs	_	2.0	_	nC	$V_{DD} = 20V, I_D = 20A, V_{GS} = 10V$	
Gate-Drain Charge	Qgd	_	1.9	_			
Turn-On Delay Time	t _{D(ON)}		5.4	_			
Turn-On Rise Time	t _R		4.5	_		V_{DD} = 20V, V_{GS} = 10V, I_D = 20A, R_g = 3 Ω	
Turn-Off Delay Time	t _{D(OFF)}	_	12.1	_	ns		
Turn-Off Fall Time	tF	_	5.6	_			
Reverse Recovery Time	t _{RR}		39.1	_	ns	1 004 11/11 4004/	
Reverse Recovery Charge	Q _{RR}	_	53.3	_	nC	I _F = 20A, di/dt = 100A/μs	

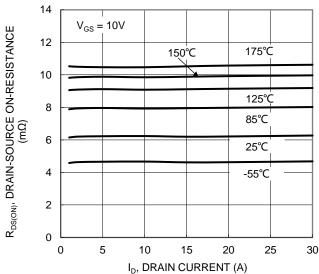
- 5. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.



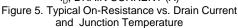








and Gate Voltage



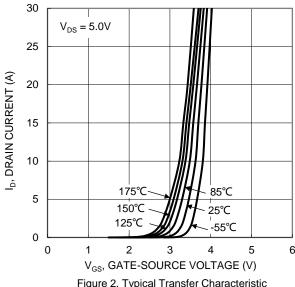
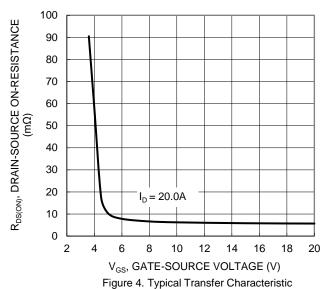


Figure 2. Typical Transfer Characteristic



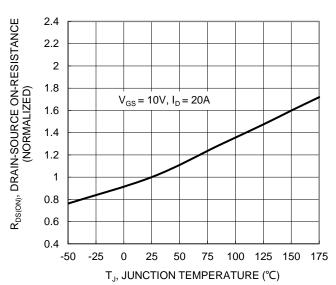
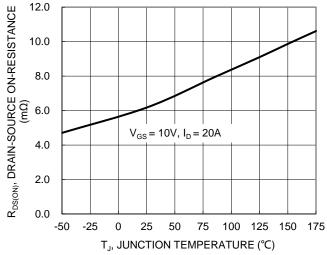
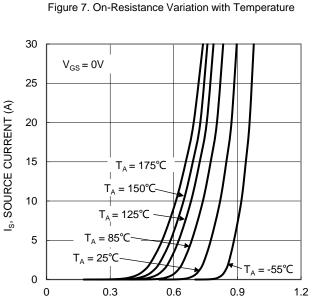


Figure 6. On-Resistance Variation with Temperature







 V_{SD} , SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

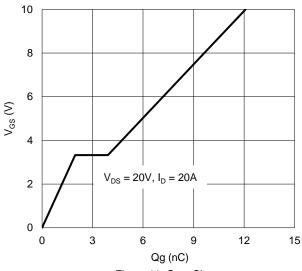


Figure 11. Gate Charge

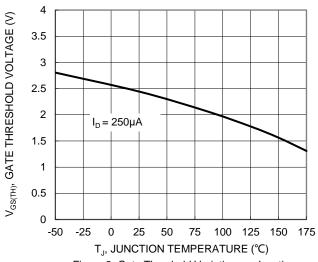
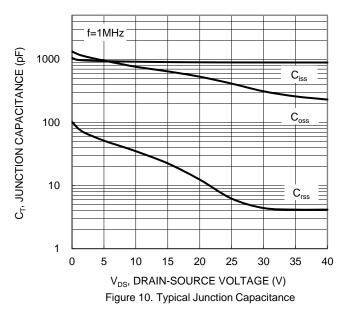


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 R_{DS(ON)} Limited 100 ID, DRAIN CURRENT (A) 10 $T_{J(Max)} = 175^{\circ}C$ $T_C = 25^{\circ}C$ 100µs $P_W = 1ms$ Single Pulse DUT on Infinite $P_W = 10ms$ Heatsink 100ms $V_{GS} = 10V$ DC 0.1 0.1 100 10 V_{DS} , DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



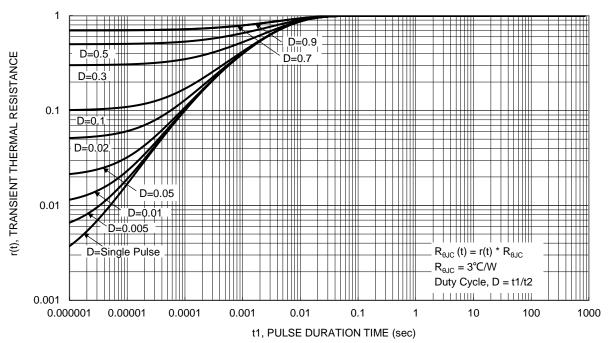


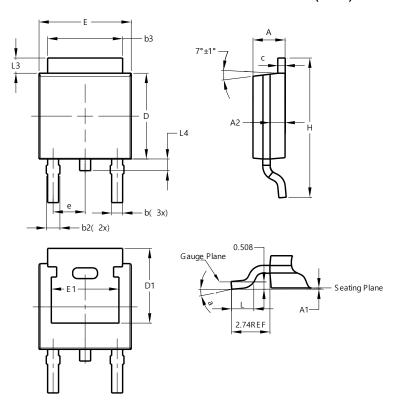
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

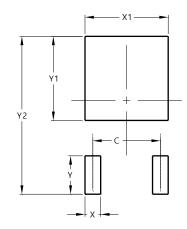


TO252 (DPAK)				
Dim	Min	Max	Тур	
Α	2.19	2.39	2.29	
A 1	0.00	0.13	0.08	
A2	0.97	1.17	1.07	
b	0.64	0.88	0.783	
b2	0.76	1.14	0.95	
b3	5.21	5.46	5.33	
С	0.45	0.58	0.531	
D	6.00	6.20	6.10	
D1	5.21	-	-	
е	-	-	2.286	
Е	6.45	6.70	6.58	
E1	4.32	-	-	
H	9.40	10.41	9.91	
٦	1.40	1.78	1.59	
L3	0.88	1.27	1.08	
L4	0.64	1.02	0.83	
а	0°	10°	-	
All Dimensions in mm				

Suggested Pad Layout

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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